Low-noise, matched dual monolithic transistor

MAT02

1.0 SCOPE

This specification documents the detail requirements for space qualified product manufactured on Analog Devices, Inc.'s QML certified line per MIL-PRF-38535 Level V except as modified herein.

The manufacturing flow described in the STANDARD SPACE LEVEL PRODUCTS PROGRAM brochure is to be considered a part of this specification http://www.analog.com/aerospace

This data sheet specifically details the space grade version of this product. A more detailed operational description and a complete datasheet for commercial product grades can be found at www.analog.com/MAT02

2.0 Part Number. The complete part number(s) of this specification follow:

Part Number	Description
MAT02-903H	Low-noise, matched dual monolithic transistor

2.1 Case Outline.

Letter	Descriptive designator	Case Outline (Lead Finish per MIL-PRF-38535)
H	MACY1-X6	6-Lead can package (TO)

Figure 1 - Terminal connections.

3.0 Absolute Maximum Ratings. (T_A = 25°C, unless otherwise noted)

Collector to base voltage (BV_{CBO}).....40V
Collector to emitter voltage (BV_{CEO}).....40V
Collector to collector voltage (BV_{CC}).....40V
Emitter to emitter voltage (BV_{EE}).....40V
Collector current (I_C).....20mA
Emitter current (I_E).....20mA
Total power dissipation 1/.....500mW
Operating ambient temperature range.....-55 to +125°C
Storage temperature range ..... -65°C to +150°C
Lead temperature (soldering, 60 sec).....+300°C
Dice junction temperature.....+150°C

1/ Rating applies to applications not using heat sinking, device is free air only.

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COMPARABLE PARTS

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DOCUMENTATION

Data Sheet

- MAT02S: Low Noise, Matched Dual Monolithic Transistor Aerospace Data Sheet

DESIGN RESOURCES

- MAT02S Material Declaration
- PCN-PDN Information
- Quality And Reliability
- Symbols and Footprints

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3.1 Thermal Characteristics:

Thermal Resistance, TO-78 (H) Package

Junction-to-Case (Θ_{JC}) = 45°C/W Max

Junction-to-Ambient (Θ_{JA}) = 150°C/W Max

Derate linearly at 6.67 mW/°C for ambient temperatures above 70°C.

Terminal Connections 1/	
Terminal	6 lead TO
1	C1
2	B1
3	E1
4	E2
5	B2
6	C2

1/ Substrate is connected to case on TO-78 package. Substrate is normally connected to the most negative circuit potential, but can be floated.

4.0 Electrical Table:

Table I

Parameter See notes at end of table	Symbol	Conditions 1/	Sub-group	Limit Min	Limit Max	Units
Current Gain	h_{FE}	I_C = 1mA; V_{CB} = 0V, 40V	1	500		
			2, 3	275		
		I_C = 100µA; V_{CB} = 0V, 40V	1	500		
		I_C = 100µA; V_{CB} = 15V	2, 3	225		
		I_C = 10µA; V_{CB} = 0V, 40V	1	400		
		I_C = 10µA; V_{CB} = 15V	2, 3	175		
		I_C = 1µA; V_{CB} = 0V, 40V	1	300		
		I_C = 1µA; V_{CB} = 15V	2, 3	150		
Current Gain Match 2/	Δh_{FE}	I_C=10µA,100µA,1mA; V_{CB}=0V	1		2	%
Offset Voltage	V_{OS}	V_{CB} = 0V	1		50	µV
			2, 3		80	
Offset Voltage vs. Temperature 5/	TCV_{OS}	V_{CB} = 0V			0.3	µV/°C
Offset Voltage vs. V_{CB} 3/	ΔV_{OS} /ΔV_{CB}	V_{CB} = 0V, 40V	1		25	µV
Offset Voltage vs. Collector Current	$\Delta V_{OS}/\Delta I_C$	V_{CB} = 0V; I_C = 10µA, 1mA	1		25	
Input Offset Current	I_{OS}	V_{CB} = 0V, 40V	1		0.6	nA
			2, 3		9.0	
Offset Current vs. V_{CB}	ΔI_{OS} /ΔV_{CB}	V_{CB} = 0V, 40V	1		70	pA/V
Bulk Emitter Resistance	r_{BE}		1		0.5	Ω

Table I(cont'd)

Parameter See notes at end of table	Symbol	Conditions 1/		Sub-group	Limit Min	Limit Max	Units
Collector Base Leakage Current	I_{CBO}	V_{CB} = 40V		1		200	pA
Collector Emitter Leakage Current 4/	I_{CES}	V_{CE} = 40V, V_{BE} = 0V		1		200	
Collector-Collector Leakage Current 4/	I_{CC}	V_{CC} = 40V		1		200	
Bias Current	I_B	V_{CB} = 0V, 40V		1		25	nA
				2, 3		60	
Collector Saturation Voltage	$V_{CE}SAT$	I_C = 1mA, I_B = 100µA		1		0.1	V
Breakdown Voltage	BV_{CEO}	I_C = 100µA		1	40		
Noise voltage density	e_n	I_C=1mA,	f_O = 10Hz	7		2	$nV/\sqrt{Hz}$
		V_{CB}=0V	f_O = 100Hz			1	
			f_O = 1000Hz			1	
			f_O = 10KHz			1	

TABLE I NOTES:

1/ V_{CB} = 15V; I_C = 10µA, unless otherwise specified.

2/ Current gain match (Δh_{FE}) is defined as: $\Delta h_{FE} = \frac{100(\Delta I_B) h_{FE}\ \min}{I_C}$

3/ Measured at I_C = 10µA and guaranteed by design over 1µA ≤ I_C ≤ 1mA.

4/ I_{CC} and I_{CES} are verified by measurement of I_{CBO}.

5/ Guaranteed by V_{OS} test $\left(TCV_{OS} \cong \frac{V_{OS}}{T} \text{ for } V_{OS} << V_{BE} \right)$ T = 298°K for T_A = +25°C.

4.1 Electrical Test Requirements:

Table II	
Test Requirements	Subgroups (in accordance with MIL-PRF-38535, Table III)
Interim Electrical Parameters	1
Final Electrical Parameters	1, 2, 3 1/ 2/
Group A Test Requirements	1, 2, 3, 7
Group C end-point electrical parameters	1 2/
Group D end-point electrical parameters	1
Group E end-point electrical parameters	1

1/ PDA applies to Subgroup 1. Delta's excluded from PDA.
2/ See Table III for delta parameters. See table I for conditions.

4.2 Table III. Burn-in test delta limits.

Table III				
TEST TITLE	BURN-IN ENDPOINT	LIFE TEST ENDPOINT	DELTA LIMIT	UNITS
h_{FE} @ 1mA	500	420	±80	
h_{FE} @ 100µA	500	410	±90	
h_{FE} @ 10µA	400	300	±100	
h_{FE} @ 1µA	300	180	±120	
IOS	0.6	1.1	±0.5	nA

5.0 Life Test/Burn-In Circuit:

5.1 HTRB is not applicable for this drawing.
5.2 Burn-in is per MIL-STD-883 Method 1015 test condition B.
5.3 Steady state life test is per MIL-STD-883 Method 1005.

Rev	Description of Change	Date
A	Initiate	Aug. 29, 2000
B	Correct typo at Dice temperature range, change RC package Θ_{JC} from 18 to 35°C/W, correct typo's on table I (subscript), make correction to Table I note 3 (change from "Measured at I_C = 10mA and guaranteed by design over 10mA ≤ I_C ≤ 1mA" to "Measured at I_C = 10μA and guaranteed by design over 1μA ≤ I_C ≤ 1mA"), add subgroup 7 for e_n, add subgroup 7 to table II, delete subgroups 4, 5, 6 from table II.	Jan. 7, 2002
C	Update web address. Delete burn-in and rad circuits	June 20, 2003
D	Update package offering	Oct. 10, 2007
E	Update header/footer & add to 1.0 Scope description.	Feb. 25,2008
F	Remove operating junction temperature line and change to Dice Junction Temperature (T_J...150°C)	March 31, 2008
G	MAT02-913H – removed because its obsolete	Sept. 23, 2014

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